

In the Claims:

1. (Currently amended) A method for removal of a barrier film on a semiconductor wafer by polishing with a polishing pad and a polishing fluid, the polishing fluid comprising abrasive particles in the range of 0.1% to 5% by weight and an acid or salt consisting of an organic acid, salt or mixture thereof in the range of 0.5-10% by weight in an aqueous solution at a pH of 7 to 12 with no addition of an oxidizing agent.
2. (Currently amended) The method as in claim 1, wherein the organic acid or salt is selected from ~~the group consisting of~~ carboxylic acids, hydrocarboxylic acids containing a hydroxyl group, ~~and amino acids~~ or salt thereof.
3. (Currently amended) The method as in claim 2, wherein the organic or salt acid is selected from ~~the group consisting of~~ citric acid, maleic acid, formic acid, acetic acid, propionic acid, butyric acid, valeric acid, acrylic acid, lactic acid, succinic acid malic acid, malonic acid, succinic acid, tartaric acid, phthalic acid, fumaric acid, lactic acid (alpha-hydroxypropionic acid or beta-hydroxypropionic acid), pimelic acid, adipic acid, glutaric acid, oxalic acid, salicylic acid, glycolic acid, tricarballic acid, ~~and benzoic acid~~ or salt thereof.
4. (Currently amended) The method as in claim 1, wherein the organic acid or salt is an amino acid or salt ~~is selected from the group consisting of~~ glutamic acid, glutamic acid hydrochloride, sodium glutamate monohydrate, glutamine, glutathione, glycylglycine, alanine, beta-alanine, gamma-aminobutyric acid, epsilon-aminocaproic acid, lysine, lysine hydrochloride, lysine dihydrochloride, lysine picrate, histidine, histidine hydrochloride, histidine dihydrochloride, aspartic acid, aspartic acid monohydrate, potassium aspartate, potassium aspartate trihydrate, tryptophan, threonine, glycine, cystine, cysteine, cysteine hydrochloride monohydrate, oxyproline, isoleucine, leucine, methionine, ornithine hydrochloride, phenylalanine, phenylglycine, proline, serine, tyrosine, valine, and a mixture or salt of these amino acids.
5. (Previously presented) The method as in claim 1, wherein the abrasive is silicon dioxide.
6. (Currently amended) The method as in claim 3, wherein the organic acid or salt is a citric acid or salt.

7. (Currently amended) The method as in claim 4, wherein the amino acid or salt is a glutamic acid or salt.
8. (Previously presented) The method as in claim 1 wherein a metal corrosion inhibitor is added to the polishing solution.
9. (Previously presented) The method as in claim 1 wherein the pH of the polishing fluid is in the range of 7 to 11.
10. (Withdrawn-currently amended) A polishing fluid for removal of a barrier film on a semiconductor wafer by polishing with a polishing pad and the polishing fluid wherein the polishing fluid comprises abrasive particles in the range of 0.1% to 5% by weight and an acid or salt consisting of an organic acid, salt or mixture thereof in the range of 0.5-10% by weight in an aqueous solution at a pH of 7 to 12 with no addition of an oxidizing agent.